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## Fax Cover Sheet

**DATE:** July 2, 2003      **PAGES:** 11 (eleven) w/cover  
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### Message

DOCKET GS 150

Please see attached: Response After Final Rejection

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*Response after Final Rejection  
Expedited Handling Requested - GAU 2826*

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Response  
110  
Patent  
10/010,484

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Hshieh et al.

Serial No.: 10/010,484

Filed: November 20, 2001

Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure

Art Unit: 2826

Examiner: Tan N. Tran

Docket No.: GS 150

**Commissioner for Patents**  
**PO Box 1450**  
**Alexandria, VA 22313-1450**

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Sir:

In response to the final Office Action dated May 3, 2003 (Paper No. 10), kindly consider the following remarks. In addition, any deficiencies may be charged to deposit account No. 50-1047.